ERRATUM

Erratum to: Progress of p-channel bottom-gate poly-Si thin-film transistor by nickel silicide seed-induced lateral crystallization

Sol Kyu Lee¹ · Ki Hwan Seok¹ · Jae Hyo Park¹ · Hyung Yoon Kim¹ ·
Hee Jae Chae¹ · Gil Su Jang¹ · Yong Hee Lee¹ · Ji Su Han¹ · Seung Ki Joo¹

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The original version of this article unfortunately contained a mistake. The presentation of Figs. 5 and 6 was incorrect. The correct Figs. 5 and 6 are given here.

The original article was corrected.

The online version of the original article can be found under doi:[10.1007/s00339-016-0133-5](https://doi.org/10.1007/s00339-016-0133-5).

✉ Seung Ki Joo
skjoo@snu.ac.kr

¹ Department of Materials Science and Engineering, Seoul National University, Seoul 151-742, Republic of Korea

Fig. 5 Gate leakage current densities (J_G) as a function of absolute value of the gate electric field (E_G) of MILC and SILC-BGPS TFTs

Fig. 6 Proano plot and grain boundary trap-state densities of MILC and SILC-BGPS TFTs